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(54) **LIGHT-EMITTING DEVICE AND  
LIGHT-EMITTING APPARATUS**

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(71) Applicant: **TIANJIN SANAN  
OPTOELECTRONICS CO., LTD.**,  
Tianjin (CN)

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(72) Inventors: **Cheng MENG**, Tianjin (CN); **Dongmei  
CAO**, Tianjin (CN); **Weihsuan LI**,  
Tianjin (CN); **Huan-Shao KUO**,  
Tianjin (CN); **Yu-Ren PENG**, Tianjin  
(CN); **Duxiang WANG**, Tianjin (CN)

(57) **ABSTRACT**

A light-emitting device includes a semiconductor epitaxial structure that has a first surface and a second surface opposite to the first surface, and that includes a first type semiconductor layer, an active layer, and a second type semiconductor layer sequentially disposed in such order in a thickness direction from the first surface to the second surface. An ohmic contact layer is disposed on the second surface of the semiconductor epitaxial structure, and a light-transmissive dielectric layer is disposed on the ohmic contact layer away from the semiconductor epitaxial structure. The light-transmissive dielectric layer has a plurality of through holes. A reflection layer is disposed on the light-transmissive dielectric layer and fills the through holes so as to be electrically connected to the ohmic contact layer.

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